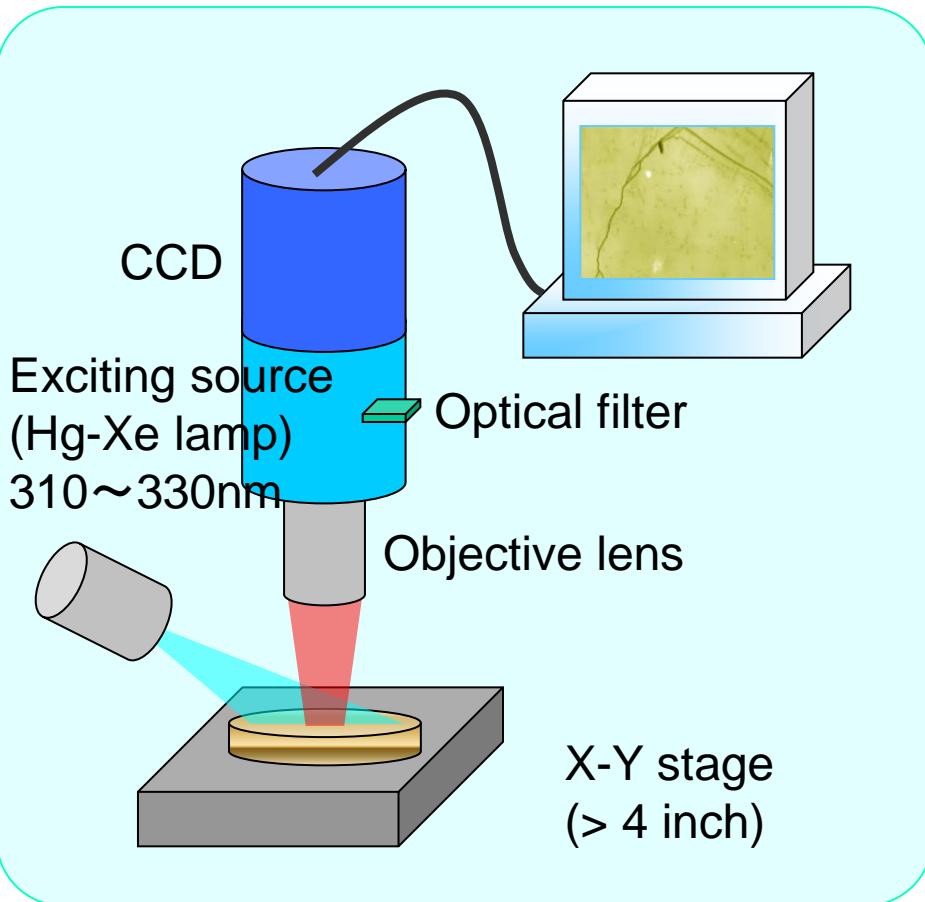
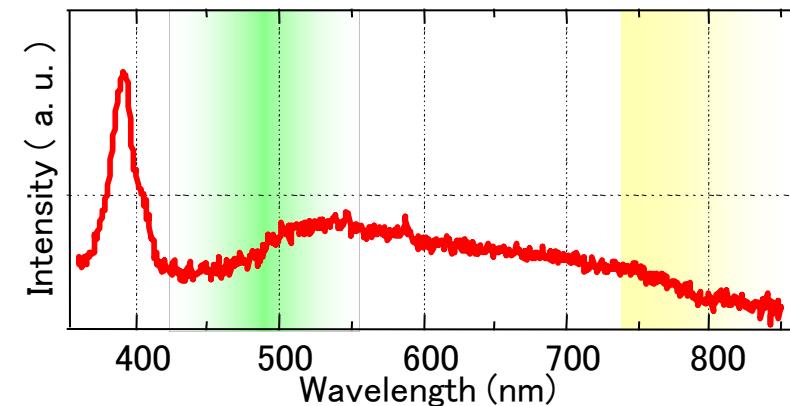
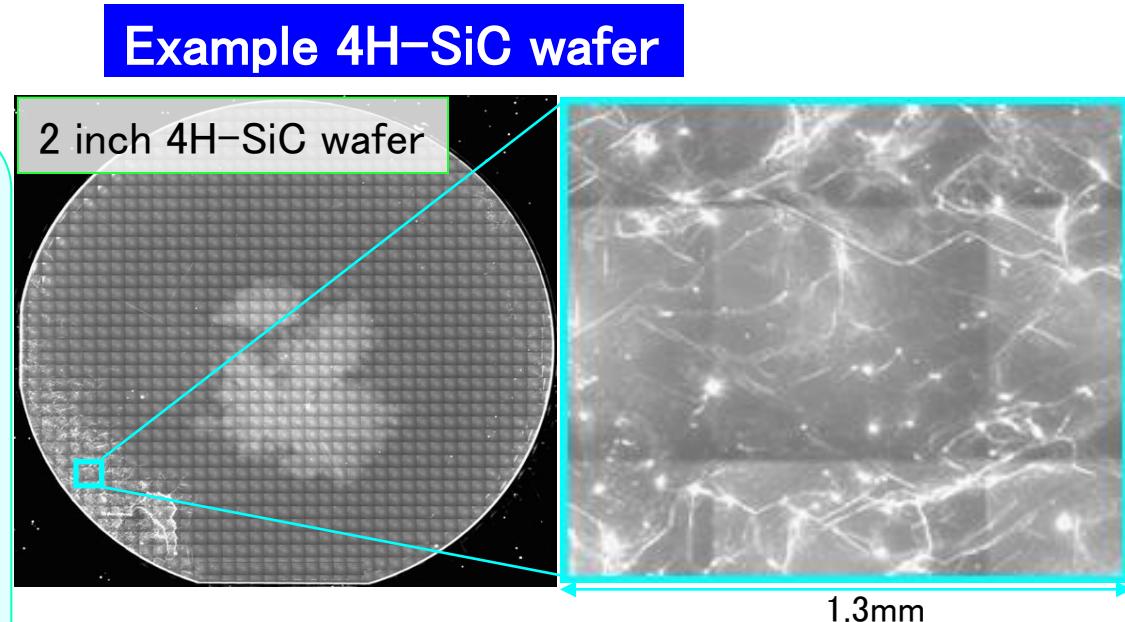


Defect evaluation by PL imaging



Schematic diagram of PL-imaging method



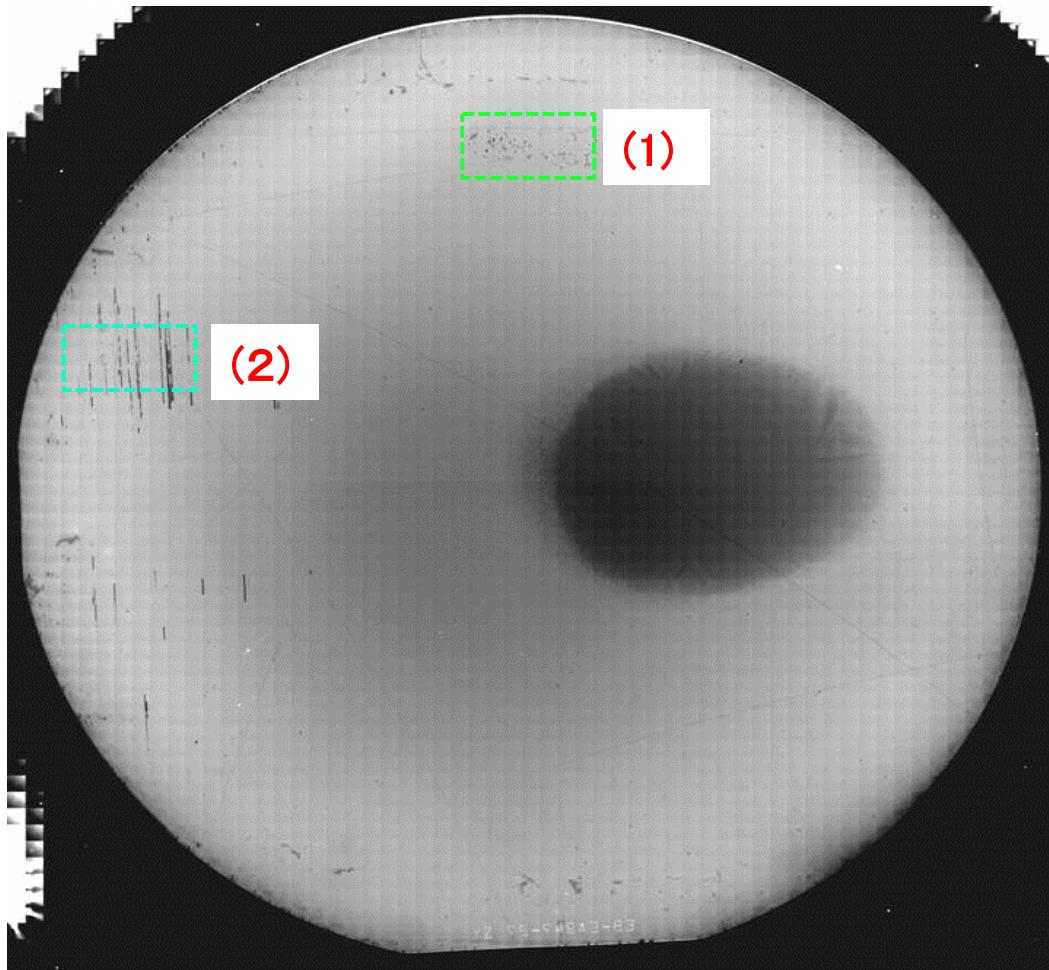
PL spectrum in 4H-SiC



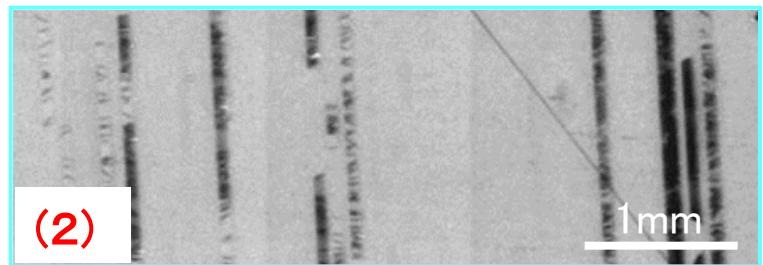
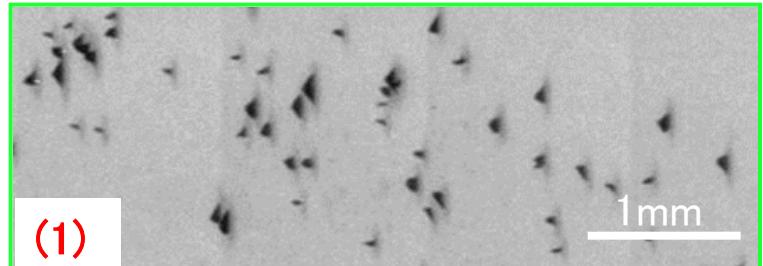
Toray Research Center, Inc.

PL image of 3-inch 4H-SiC wafer

Sample:4H-SiC (3 inch)



PL image ($\lambda > 325\text{nm}$)



Toray Research Center, Inc.

S00264構造化学第1研究室20141001 STC:開(20141121)